

# TRACER

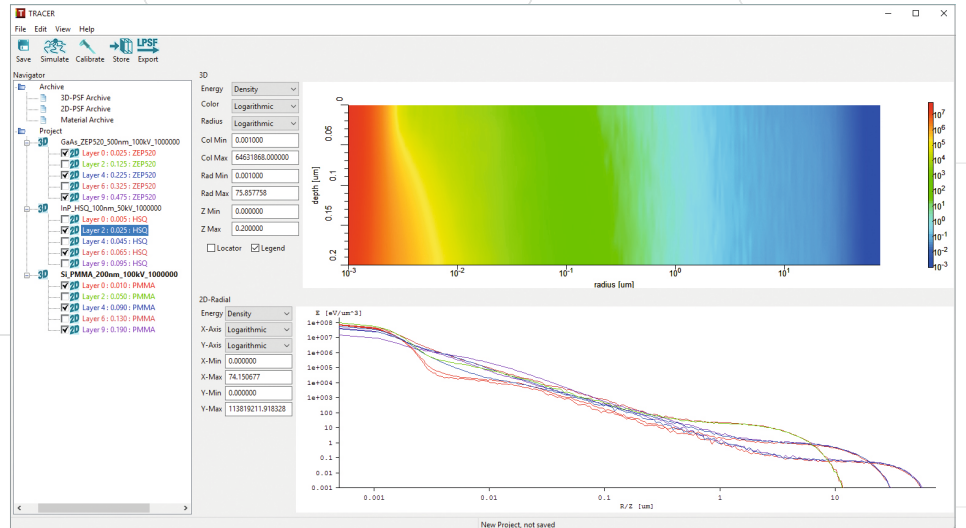
Advancing the Standard

## Electron Scattering and Process Effects Quantified

**TRACER** is a Monte Carlo simulator that computes the electron-solid interaction of any arbitrary material stack and performs advanced process calibration for electron beam proximity effect correction.

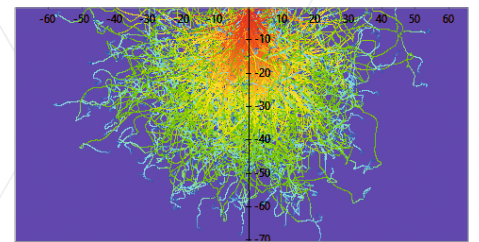
Fast, Easy and Accurate  
PSF Simulation and  
Visualization

Manage, Maintain  
and Archive all PSFs  
with an Interface to  
BEAMER & LAB



A Point Spread Function (PSF) is the essential input for any type of Proximity/Process Effect Correction (PEC) or e-beam simulation. A PSF describes the deposited energy as a function of the distance from the incident beam. In other words, a PSF can be described as the convolution of the electron scattering beam size (or beam blur) and process effects, which can include collateral effects from resist development and pattern transfer. The quality of a process effect correction depends entirely on the knowledge of the PSF and process correction parameters such as base dose and process bias. As such, a necessary starting point is a high-quality Monte Carlo (MC) simulation of not only electrons backscattered from the substrate, but also fast secondary electrons from both the primary exposure and backscattering events.

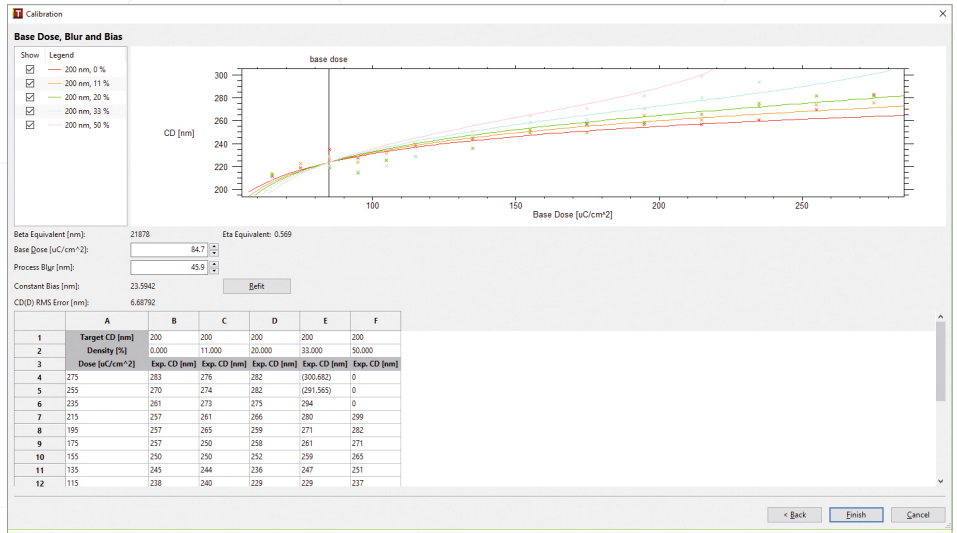
**TRACER** offers an easy-to-use interface for defining the required parameters (material data, stack parameters, acceleration voltage), running the MC simulation, visualizing the 2D r-z simulation results (energy spread at different resist thicknesses), and extracting the 1D PSF which can then be used for PEC.



The comprehensive material database includes all standard materials and can easily be expanded with custom materials by defining the new material's stoichiometry and mass density. Functionalities such as fitting to Gaussian functions, averaging, convolution of PSFs, determination of base-dose factors between PSFs and powerful visualization enable the user to analyze, compare and optimize PSFs.

Material	Name	Mass Density [g/cm <sup>3</sup> ]	Excitation Energy [eV]	Stoichiometry	Optional
1	Ag	10.500000	470.000000	Ag 1	Ce 108 - D1 1 - Ep 58.7114 - La 1.86
2	Al	2.698900	165.000000	Al 1	Ce 61 - D1 1 - Ep 22.8379 - La 2.538
3	AlAs	3.700000	281.729400	Al 1 - As 1	Ce 5 - D1 11
4	AlGaAs_15	5.088000	333.437700	Al 15 - Ga 85 - As 100	Ce 0 - D1 11
5	AlGaAs_30	4.072000	293.879500	Al 30 - Ga 20 - As 100	Ce 0 - D1 11
6	AlN	3.230000	129.889000	Al 1 - N 1	Ce 5 - D1 8.5
7	Alumina	3.970000	145.200000	Al 2 - O 3	Ce 0 - D1 10 - Ep 20.8213 - La 3.748
8	Au	19.300000	790.000000	Au 1	Ce 73 - D1 6.5 - Ep 44.2985 - La 3.184
9	C	2.180000	100.000000		
10	Cu2O3	5.230000			
11	Cu	8.960000			
12	Fe	7.874000			
13	GaAs	5.310000			
14	GaInAs_47	5.500000			
15	GaN	6.190000			
16	Ge	5.323000			
17	HEES_gfms	2.700000			
18	InAs	5.600000			
19	InP	4.784000			
20	InGa03	4.840000			
21	LiFeO3	7.450000			
22	Mn	10.220000			
23	Ni	8.910000			
24	Pt	21.450000			
25	PZT	7.550000			
26	Quartz_Glass	2.200000			
27	Sapphire	3.970000			
28	Si	2.330000			
29	Si3N4	3.200000			
30	SiC	3.210000			
31	SiO2	2.650000			

In addition tool and process effects such as spot size, lateral development, resist diffusion and loading effects need to be quantified and corrected. **TRACER** has an easy-to-use Calibration feature which determines and corrects these effects using measured CD data (typically CD as a function of dose and layout density) obtained after processing of a calibration pattern. Process parameters such as base dose, process blur and process bias are rapidly computed and the display of calibration versus measured data allows the user to immediately verify the fit quality.



## TRACER Major Features

### Monte Carlo Simulation

- Easily-defined stack
- User-defined number of electrons
- Automatic or custom grid spacing
- Live updating during simulation
- Store a PSF directly into the library shared with **BEAMER**

### Analysis & Computation

- Model fitting with 2–4 Gaussians
- Averaging of PSFs
- Convolution of PSFs
- Calculation of relative base dose between PSFs

### Visualization

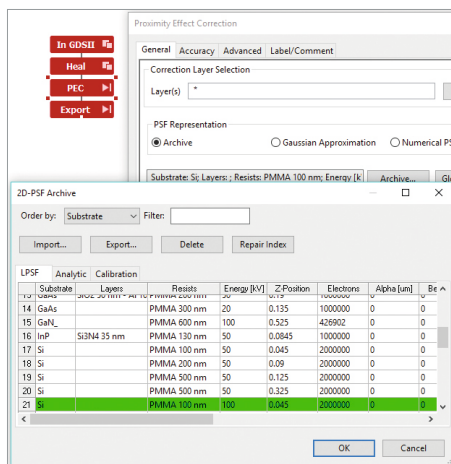
- 2-D and 1-D plotting of energy distribution
- Electron trajectory plots
- Highly-customizable plots

### Material Library

- Library of common materials
- Metals, semiconductors, insulators, resists
- Easy for users to add additional materials

### Process Calibration

- Based on exposure and measurement of critical CD through dose and density
- Determines base dose, process blur, process/metrology bias, lateral development
- Usable by **BEAMER** to correct for full process effects
- 2-Stage fitting for more accurate results



GenISys products share highly dedicated support, have flexible licensing and are available on various platforms/operating systems.

### Flexible licensing and platform support

- USB license key for dongle and network
- Flexible on off-the-shelf PCs (> 4 GB RAM recommended)
- Windows 7/8/10 64bit, Linux64 Red Hat 5.4+, Ubuntu 14.04+
- Multithreading

### Maintenance and Support

- Technical Support Hotline (e-mail, Skype, phone)
- Frequent updates with enhancements, new functions, performance tuning and bug fixes
- Regional trainings, technical workshops, user meetings
- 12 month maintenance service included in license price
- User feature requests are high-priority for implementation in future updates

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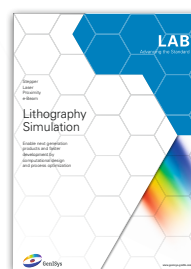
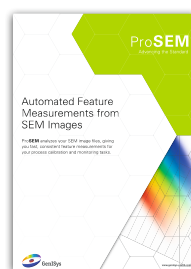
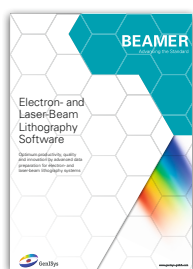


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Based in Munich, Germany, with offices in Tokyo, Japan and California, USA, **GenISys** develops, markets and supports flexible, high-performance software solutions for the optimization of micro- and nano-fabrication processes. Addressing the market for lithography and inspection, **GenISys** combines deep technical expertise in layout data processing, process modeling, correction and optimization with high caliber software engineering coupled with a focus on ease of use.

The **GenISys** software suite provides researchers, manufacturers and system suppliers with unparalleled, efficient, ease-of-use solutions to advance the research, development and production of next generation nano-patterning technologies.

As a company focused on customer service, **GenISys** provides fast, highly dedicated support for the application and development of the functionality needed to meet demanding customer requirements.